

FQB46N15 / FQI46N15

150V N-Channel MOSFET

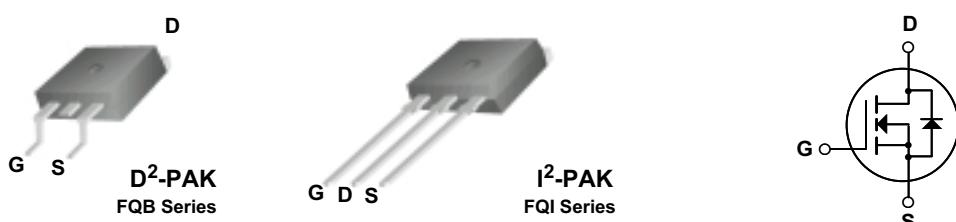
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.

Features

- 45.6A, 150V, $R_{DS(on)} = 0.042\Omega$ @ $V_{GS} = 10$ V
- Low gate charge (typical 85 nC)
- Low C_{RSS} (typical 100 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB46N15 / FQI46N15	Units
V_{DSS}	Drain-Source Voltage	150	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	45.6	A
	- Continuous ($T_C = 100^\circ\text{C}$)	32.2	A
I_{DM}	Drain Current - Pulsed	(Note 1)	A
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	mJ
I_{AR}	Avalanche Current	(Note 1)	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.75	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	210	W
	- Derate above 25°C	1.43	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	--	0.16	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 150 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$	--	--	1	μA
		$V_{\text{DS}} = 120 \text{ V}$, $T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = 25 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = -25 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
On Characteristics						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = 250 \mu\text{A}$	2.0	--	4.0	V
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 22.8 \text{ A}$	--	0.033	0.042	Ω
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 40 \text{ V}$, $I_D = 22.8 \text{ A}$ (Note 4)	--	33	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}} = 25 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	--	2500	3250	pF
C_{oss}	Output Capacitance		--	520	670	pF
C_{rss}	Reverse Transfer Capacitance		--	100	130	pF
Switching Characteristics						
$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 75 \text{ V}$, $I_D = 45.6 \text{ A}$, $R_G = 25 \Omega$	--	35	80	ns
t_r	Turn-On Rise Time		--	320	650	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	210	430	ns
t_f	Turn-Off Fall Time		--	200	410	ns
Q_g	Total Gate Charge	$V_{\text{DS}} = 120 \text{ V}$, $I_D = 45.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$	--	85	110	nC
Q_{gs}	Gate-Source Charge		--	15	--	nC
Q_{gd}	Gate-Drain Charge		--	41	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	45.6	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	182.4	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 45.6 \text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 45.6 \text{ A}$, $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	130	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.55	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 0.52mH, $I_{AS} = 45.6\text{A}$, $V_{DD} = 25\text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{sp} \leq 45.6\text{A}$, $dI/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq \text{BV}_{\text{DSS}}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

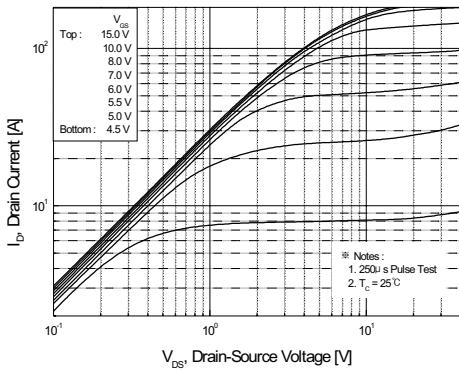


Figure 1. On-Region Characteristics

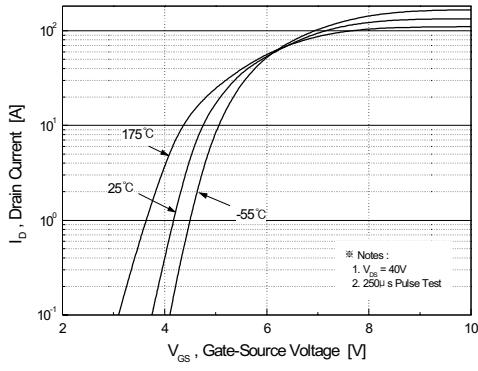


Figure 2. Transfer Characteristics

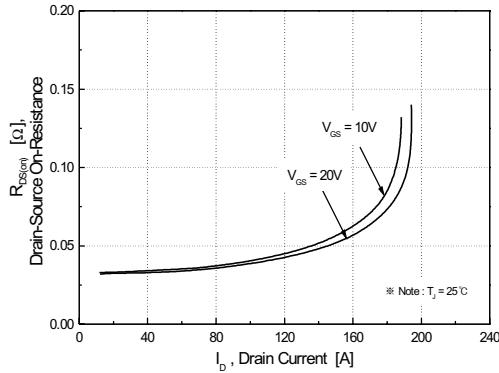


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

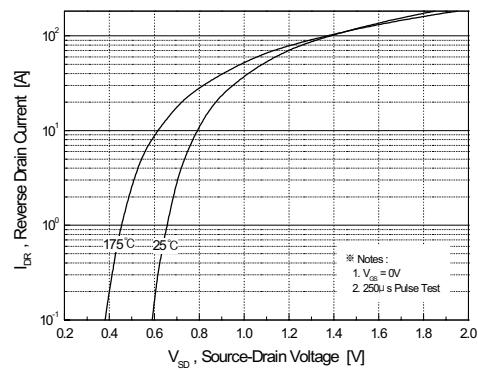


Figure 4. Body Diode Forward Voltage
Variation vs. Source Current
and Temperature

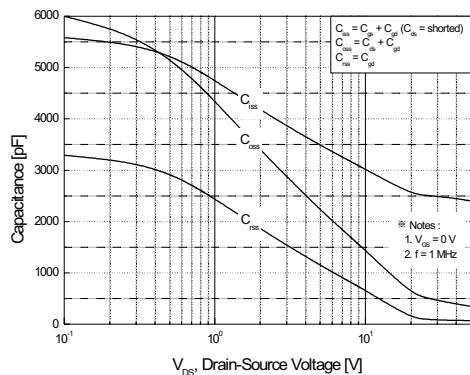


Figure 5. Capacitance Characteristics

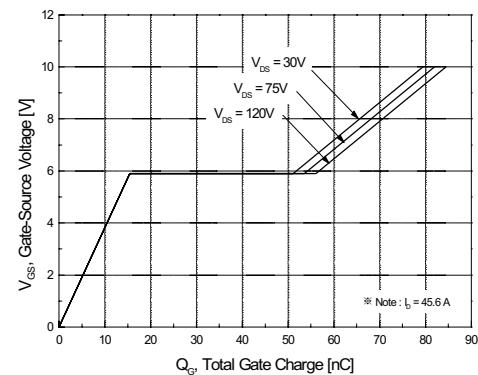


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

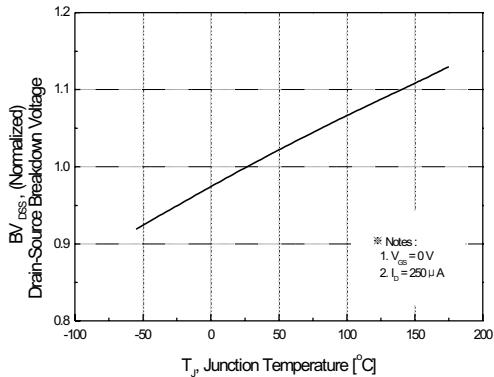


Figure 7. Breakdown Voltage Variation vs. Temperature

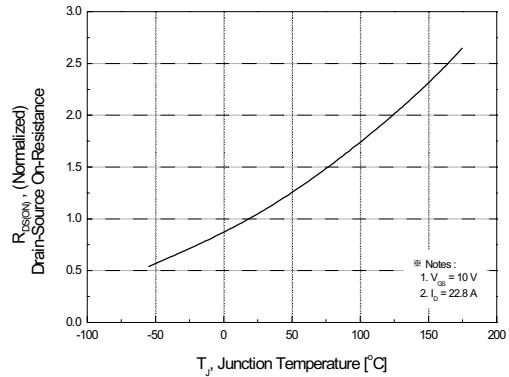


Figure 8. On-Resistance Variation vs. Temperature

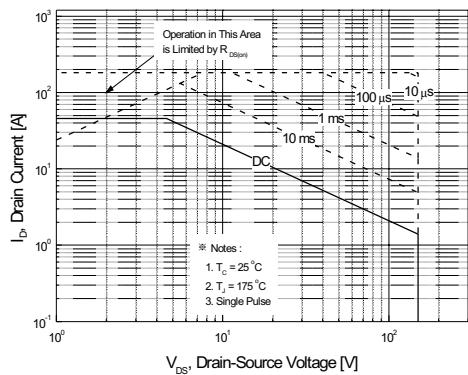


Figure 9. Maximum Safe Operating Area

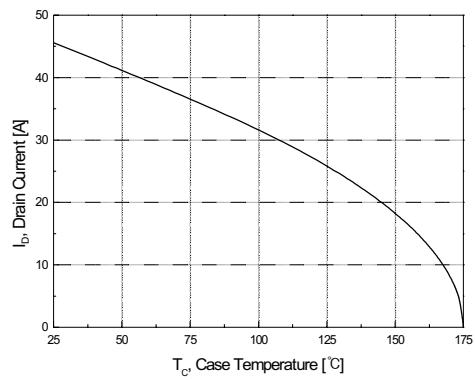


Figure 10. Maximum Drain Current vs. Case Temperature

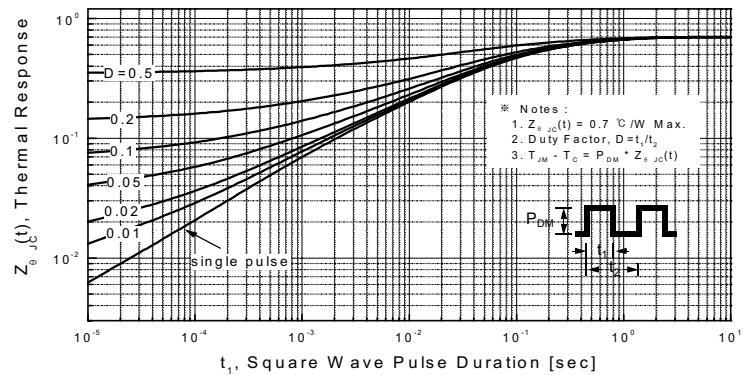
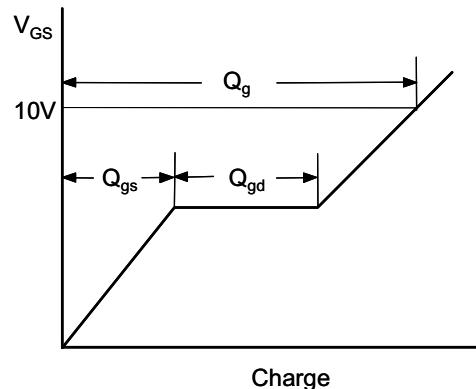
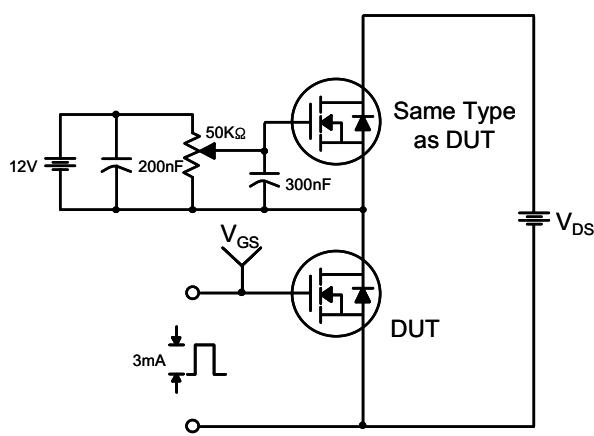
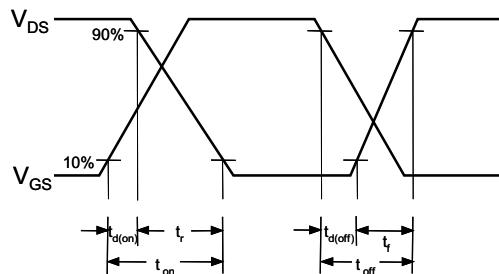
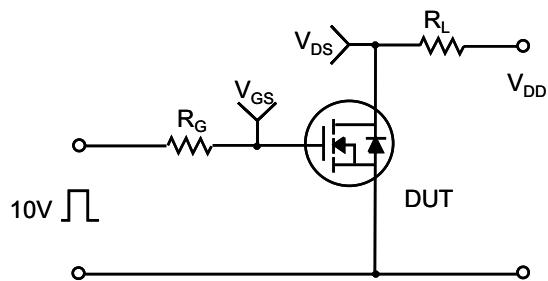


Figure 11. Transient Thermal Response Curve

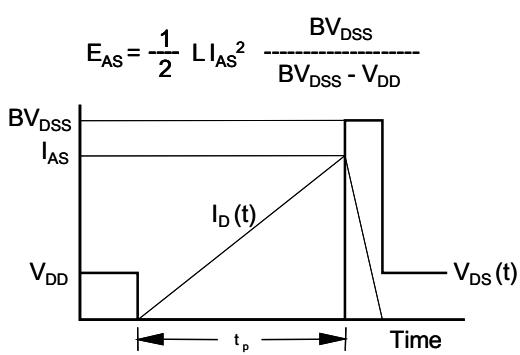
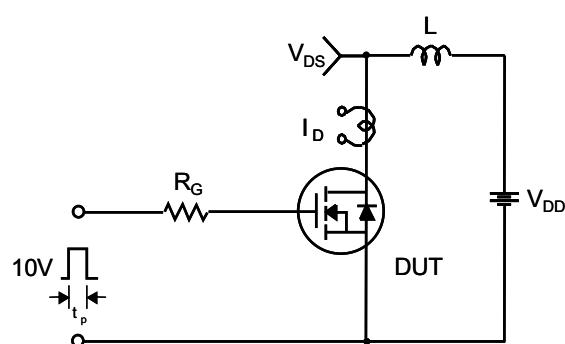
Gate Charge Test Circuit & Waveform



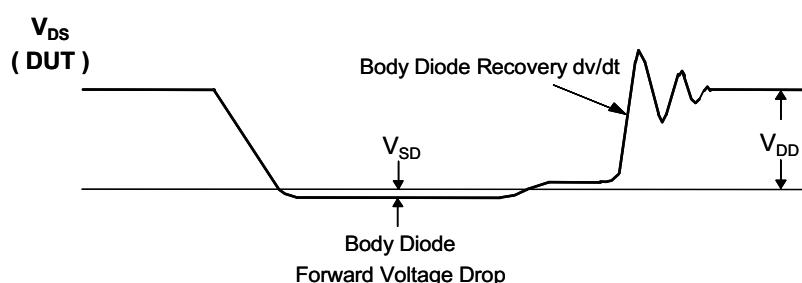
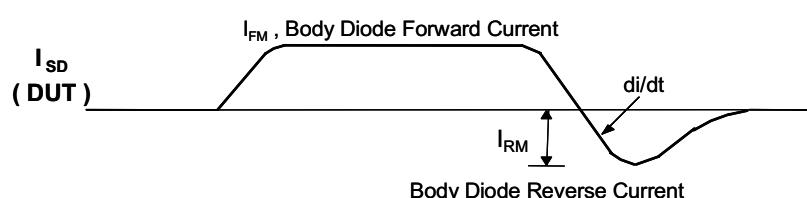
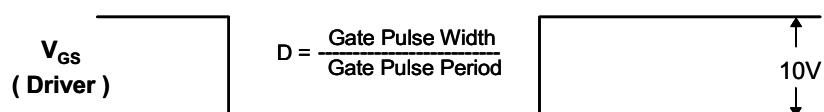
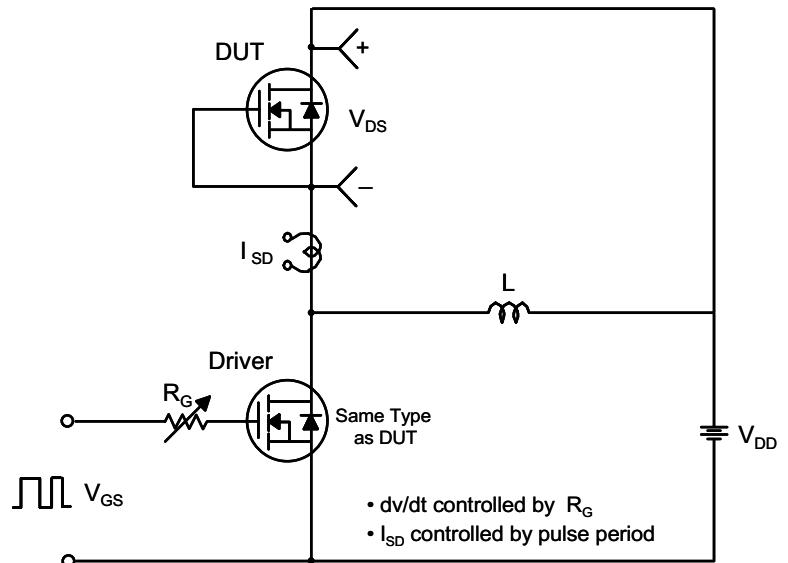
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

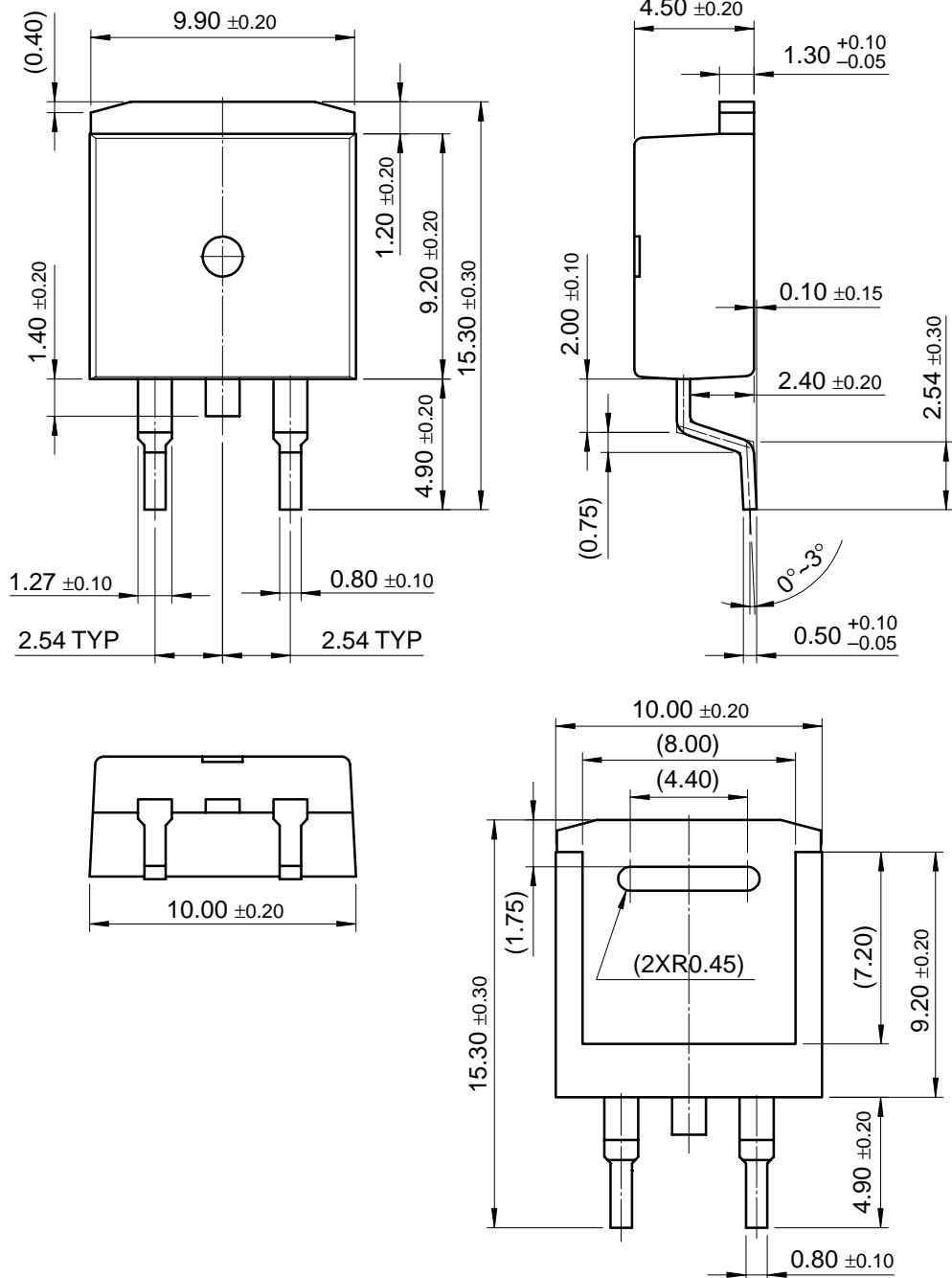


Peak Diode Recovery dv/dt Test Circuit & Waveforms

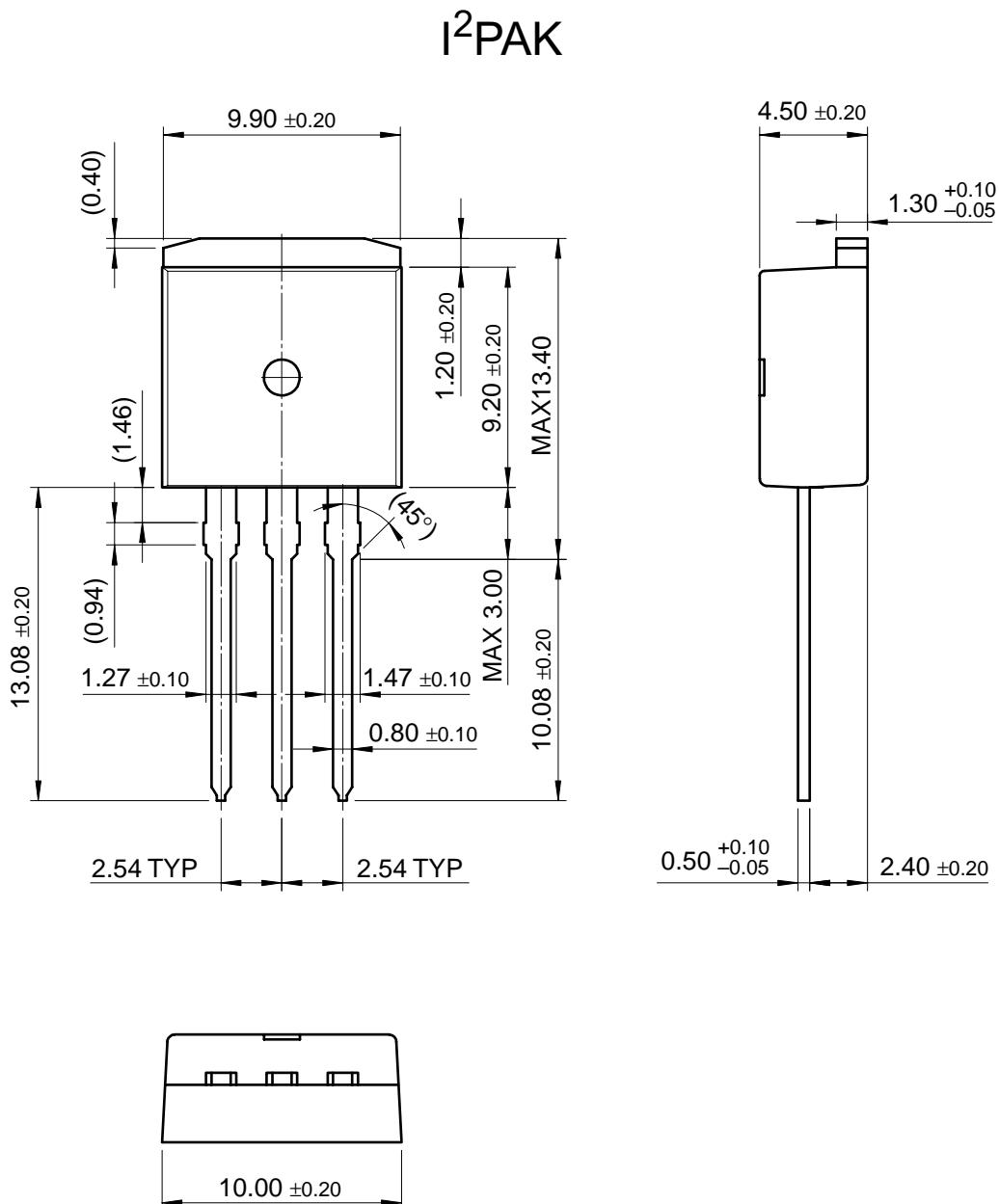


Package Dimensions

D²PAK



Package Dimensions (Continued)



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